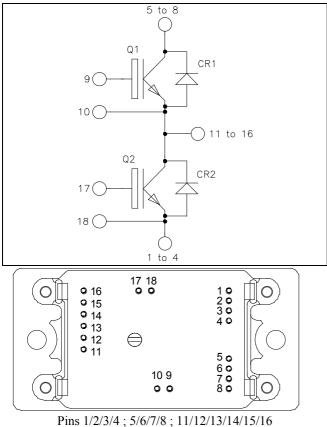


APTGF100A1202G

Phase leg NPT IGBT Power Module



must be shorted together

$V_{CES} = 1200V$ $I_C = 100A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

All ratings (a) $T_i = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
I _C	Continuous Collector Current	$T_c = 25^{\circ}C$	135	
	Continuous Conector Current	$T_c = 80^{\circ}C$	100	А
I _{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	300	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_c = 25^{\circ}C$	568	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	200A @ 1200V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μA
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		3.2	3.7	V
		$I_{\rm C} = 100 {\rm A}$	$T_{j} = 125^{\circ}C$		3.9		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 4mA$		4.5	5.5	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

Dynamic Characteristics

v	Characteristic	Test Condition	Test Conditions		Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			6.5		nF
C _{oes}	Output Capacitance				1		
Cres	Reverse Transfer Capacitance	f = 1 MHz	f = 1 MHz		0.5		
Q _G	Gate charge	$V_{GE} = \pm 15V$; V $I_C = 100A$	$V_{GE} = \pm 15V$; $V_{CE} = 600V$ $I_{C} = 100A$		1.1		μC
T _{d(on)}	Turn-on Delay Time	Inductive Swite	ching (25°C)		120		
T _r	Rise Time	$V_{GE} = \pm 15V$			50		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600 V$ $I_{C} = 100 A$	$V_{Bus} = 600V$ $L_c = 100A$		310		ns
T _f	Fall Time	$R_G = 5.6\Omega$		20			
T _{d(on)}	Turn-on Delay Time		Inductive Switching (125°C)		130		ns
T _r	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_{C} = 100A$			60		
T _{d(off)}	Turn-off Delay Time				360		
$T_{\rm f}$	Fall Time	$R_G = 5.6\Omega$	-		30		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_{j} = 125^{\circ}C$		12		T
E _{off}	Turn-off Switching Energy	$I_{C} = 100A$ $R_{G} = 5.6\Omega$	$T_j = 125^{\circ}C$		5		mJ
I _{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 900V$ $t_p \le 10\mu s$; $T_1 = 125^{\circ}C$			650		А
R _{thJC}	Junction to Case Thermal Resistance					0.19	°C/W

Reverse diode ratings and characteristics

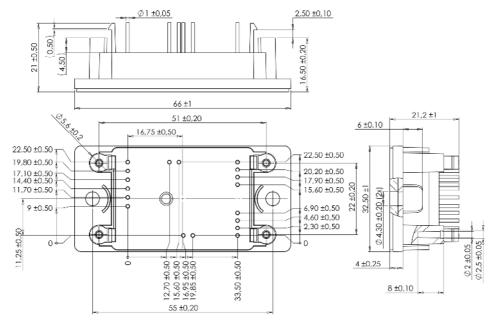
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V				250	μΑ
I _F	DC Forward Current		$Tc = 80^{\circ}C$		100		Α
	Diode Forward Voltage	$I_{\rm F} = 100 {\rm A}$			2.4	3	V
$V_{\rm F}$		$I_F = 150A$			2.7		
		$I_{\rm F} = 100 {\rm A}$	$T_{j} = 125^{\circ}C$		1.8		
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		385		20
		$I_F = 100A$ $V_R = 800V$ $T_j = 125^{\circ}$	$T_{j} = 125^{\circ}C$		480		ns
Q _{rr}	Reverse Recovery Charge	$di/dt = 200 \text{ /} \mu \text{s}$	$T_j = 25^{\circ}C$		1055		nC
			$T_{j} = 125^{\circ}C$		5240		ne
R _{thJC}	Junction to Case Thermal Resistance					0.55	°C/W



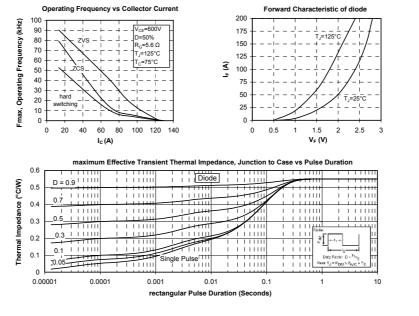
Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					75	g

SP2 Package outline (dimensions in mm)



Typical Performance Curve

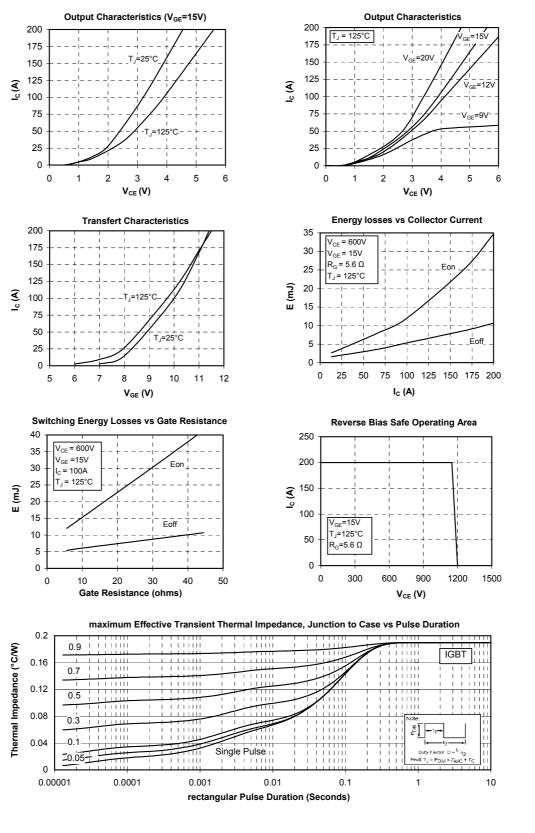


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